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部分习题答案

第1章

- 1.2.1 (1) $v(t) = 5 \sin(2 \times 10^4 \pi t)$ (V); (2) $v(t) = 220\sqrt{2} \sin(100\pi t)$ (V);
(3) $v(t) = 0.05 \sin(2000\pi t)$ (V); (4) $v(t) = 0.125 \sin(1000t)$ (V);

1.2.2 $\frac{V_s^2}{4R}, \frac{2V_s^2}{\pi^2 R}, \frac{2V_s^2}{9\pi^2 R}, 95\%$

- 1.4.1 (1) 8.26; (2) 2.5; (3) 0.0826; (4) 0.826

- 1.5.1 200, 46 dB; 100, 40 dB; 20 000, 43 dB

- 1.5.2 250 Ω

- 1.5.3 100 Ω

- 1.5.4 800, 58 dB; 2 000, 66 dB; 1.6×10^6 , 62 dB

- 1.5.6 $R_1/(\beta + 1)$

- 1.5.7 0.708

第2章

- 2.1.1 (1) $\pm 10 \mu\text{V}$; (2) $\pm 1 \times 10^{-8} \mu\text{A}$

- 2.1.2 v_o 不能小于 -11 V

- 2.3.1 图 a 6 V; 图 b 6 V; 图 c +2 V; 图 d +2 V

- 2.3.2 图 a $v_o = 4$ V, $i_1 = i_2 = 0.33$ mA, $i_3 = i_4 = -0.2$ mA, $i_o = 1$ mA; 图 b $v_o = -150 \sin\omega t$ (mV), $i_2 = i_1 = 10 \sin\omega t$ (μA), $i_o = -40 \sin\omega t$ (μA); 图 c $v_{oi} = -1.2$ V, $v_o = 1.8$ V

- 2.3.3 (1) $R_{1\min} = 8$ kΩ, $R_{2\min} = 92$ kΩ; (2) $R_1 = 50$ kΩ, $R_2 = 400$ kΩ

- 2.3.5 (1) $V_C = 6$ V, $V_B = 0$ V, $V_E = -0.7$ V; (2) $\beta = 50$

2.4.1 $\frac{R_2}{R_1} \left(\frac{-\delta}{4 + 2\delta} \right) v_i$

2.4.2 $-(R_2 R_4 / R_1 R_3)$

2.4.3 $R_2 = 200 \text{ k}\Omega$, $R_3 = R_4 = 51 \text{ k}\Omega$, $R_p = 100 \text{ k}\Omega$, $R_1 = R'_1 + R_p = (1 + 100) \text{ k}\Omega$

2.4.4 $R_5 = 280 \text{ k}\Omega$, $R_1 = 40 \text{ k}\Omega$, $R_2 = 20 \text{ k}\Omega$, $R_3 = 80 \text{ k}\Omega$, $R_4 = 28 \text{ k}\Omega$

2.4.5 (1) $v_o = \left(1 + \frac{R_4}{R_3}\right) \left(\frac{1}{R_1 + R_2}\right) (R_2 v_{ii} + R_1 v_{i2})$, $v_o = v_{ii} + v_{i2}$

(2) $v_o = \frac{R_2 R_3 v_{ii} + R_1 R_3 v_{i2} + R_1 R_2 v_{i3}}{R_1 R_2 + R_2 R_3 + R_1 R_3}$, $v_o = \frac{1}{3} (v_{ii} + v_{i2} + v_{i3})$

2.4.6 $v_o = -(5/4)v_{ii} - 2v_{i2} + (51/22)v_{i3} + (51/44)v_{i4}$

2.4.7 $v_{o1} = -3 \text{ V}$, $v_{o2} = 4 \text{ V}$, $v_o = 5 \text{ V}$

2.4.8 (1) $v_o = -5 \text{ V}$; (2) v_{o1} 的幅值 $\sim 7.66 \text{ V}$, 回零时间 $t = 120 \text{ ms}$

2.4.9 (1) $v_{o1} = \left(\frac{R_3}{R_2 + R_3}\right) \left(1 + \frac{R_4}{R_1}\right) v_{i2} - \frac{R_4}{R_1} v_{ii}$, $v_o = -\frac{1}{C} \int_0^t \left(\frac{v_{o1}}{R_5} + \frac{v_{i3}}{R_6}\right) dt$

(2) $v_o = -\frac{1}{RC} \int_0^t [(v_{i2} - v_{ii}) + v_{i3}] dt$

2.4.10 (1) $v'_o = \frac{1}{RC} \int_0^t v_{i2} dt$; (2) $v''_o = -\frac{1}{RC} \int_0^t v_{ii} dt$; (3) $v_o = \frac{1}{RC} \int_0^t (v_{i2} - v_{ii}) dt$

2.4.11 v_o 的幅值为 $\pm 0.1 \text{ V}$

2.4.12 (1) $\frac{V_o(s)}{V_i(s)} = -\frac{sR_2 C_1}{(1 + sR_1 C_1)(1 + sR_2 C_2)}$; (2) $f \ll f_H = \frac{1}{2\pi RC}$

2.4.13 (1) $A_V(s) = -\left(\frac{R_2}{R_1} + \frac{1}{sR_1 C}\right)$

2.4.14 (1) $v_{o1} = +0.3 \text{ V}$, $v_{o2} = -\frac{1}{10s} \int_0^t v_{i2} dt$, $v_o = -0.3 \text{ V} + \frac{1}{10s} \int_0^t v_{i2} dt$

第3章

3.2.1 0.34 V

3.4.3 (1) 8.6 mA, 1.4 V; (2) 1.406 V ~ 1.394 V

3.4.4 1.393 ~ 1.407 V

3.4.5 -6 V, -12 V, 0 V, -6 V

3.4.6 (a) 截止; (b) 截止; (c) 导通

3.4.10 (1) 1.3 mA, 1.3 V; (2) 49 μA, 49 mV; (3) $1.3 + 0.049 \sin(2\pi \times 50t) \text{ (V)}$

3.5.2 (1) $V_z \left(\frac{V_L - V_z}{R} - \frac{V_z}{R_L} \right)$; (2) $\frac{V_z^2}{R_L}$, $\frac{(V_L - V_z)^2}{R}$

3.5.3 (1) 大于 111 Ω; (2) 225 mW; (3) 250 mW, 250 mW

SP3.6.1 0.34 V

SP3.6.2 62.56

SP3.6.4 小于 170 mA

第4章

4.1.1 A - c、B - e、C - b; PNP 管

- 4.1.2 A - c、B - b、C - e; NPN 管; $\beta = 50$
- 4.1.3 $I_C = 15 \text{ mA}$; 电压为 30 V
- 4.2.1 (a) 无; (b) 有; (c) 无; (d) 无
- 4.2.2 S→A: 饱和区; $I_C = 3 \text{ mA}$
 S→B: 放大区; $I_C = 1.92 \text{ mA}$
 S→C: 截止区; $I_C = 0$
- 4.2.3 (a) 放大区; (b) 放大区; (c) 饱和区; (d) 截止区; (e) 饱和区
- 4.3.1 $\beta = 200$; $V_{CES} = 0.8 \text{ V}$
- 4.3.2 $I_{CQ} = 4 \text{ mA}$, $V_{CEQ} = 9 \text{ V}$
- 4.3.3 $I_{BQ} = 0.03 \text{ mA}$, $I_{CQ} = 6 \text{ mA}$, $V_{CEQ} = 6 \text{ V}$
- 4.3.4 $I_{BQ} = 0.125 \text{ mA}$, $I_{CQ} = 25 \text{ mA}$, $V_{CEQ} = 1 \text{ V}$
- 4.3.5 (1) $V_{CC} = 6 \text{ V}$, $I_{BQ} = 20 \mu\text{A}$, $I_{CQ} = 1 \text{ mA}$, $V_{CEQ} = 3 \text{ V}$
 (2) $R_b = 300 \text{ k}\Omega$, $R_e = 3 \text{ k}\Omega$
 (3) $V_{om} = 1.5 \text{ V}$
 (4) $i_{bm} = 20 \mu\text{A}$
- 4.3.6 设 BJT 为硅管, 在放大区时应有 $|v_{CE}| \geq 1 \text{ V}$, $|v_{BE}| = 0.7 \text{ V}$, 故应该使 $v_B = (v_E - 0.7) \text{ V}$, 其中 $v_E \geq -2.67 \text{ V}$
- 4.3.7 因为 $\beta = 100 \gg 1$, 故有 $i_E \approx i_C$, 依题意 $R_e \approx 0.83R_o$
- 4.3.9 (1) $I_{BQ} = 40 \mu\text{A}$, $I_{CQ} = 2 \text{ mA}$, $V_{CEQ} = 4 \text{ V}$
 (3) $r_{be} = 863 \Omega$
 (4) $A_v \approx -116$, $A_{vs} \approx -73$
- 4.3.10 $R_b = 240 \text{ k}\Omega$, $R_o \geq 3.75 \text{ k}\Omega$, $V_{CEQ} = 8.25 \text{ V}$
- 4.3.11 (1) $I_{BQ} = 40 \mu\text{A}$, $I_{CQ} = 4 \text{ mA}$, $V_{CEQ} = -4 \text{ V}$
 (2) $A_v \approx -155.6$, $R_i \approx 0.86 \text{ k}\Omega$, $R_o \approx 2 \text{ k}\Omega$
 (4) 截止失真; 减小 R_b
- 4.3.12 (1) $I_{CQ} \approx \beta V_{CC}/R_1$, $V_{CEQ} = V_{CC} - I_{CQ}(R_2 + R_3)$
 (2) $A_v = -\beta(R_2 \parallel R_L)/r_{be}$, $R_i = R_1 \parallel r_{be}$, $R_o \approx R_2$
 (3) 使 $|A_v|$ 增加, R_o 增大
- 4.4.1 (1) $I_{BQ} \approx 15 \mu\text{A}$, $I_{CQ} = 0.9 \text{ mA}$, $V_{CEQ} = 5.88 \text{ V}$
 (2) $\beta = 75$, $V_{BEQ} = 0.6 \text{ V}$, $I_{BQ} \approx 15.2 \mu\text{A}$, $I_{CQ} = 1.14 \text{ mA}$, $V_{CEQ} \approx 4.25 \text{ V}$
 (3) $I_{BQ} \approx 15 \mu\text{A}$, $I_{CQ} = 1.73 \text{ mA}$, $V_{CEQ} = 0.24 \text{ V}$, BJT 进入饱和区
- 4.4.2 图(a)能; 图(b)不能
- 4.4.3 (1) $I_{BQ} \approx 28 \mu\text{A}$, $I_{CQ} = 1.65 \text{ mA}$, $V_{CEQ} = 7.8 \text{ V}$
 (2) $r_{be} \approx 1.2 \text{ k}\Omega$
 (3) $A_v \approx -100$
 (4) $R_{bl} \approx 38.2 \text{ k}\Omega$
- 4.4.4 (2) $R_i \approx 4.6 \text{ k}\Omega$, $R_o \approx 3.3 \text{ k}\Omega$; (3) $v_o \approx -124.5 \text{ mV}$
- 4.4.5 (1) $R_e = 14.3 \text{ k}\Omega$; (2) $R_e = 10 \text{ k}\Omega$; (3) $A_{vs} \approx -100$

- 4.4.6 (1) $I_{BQ} \approx 12.7 \mu\text{A}$, $I_{CQ} \approx 1.27 \text{ mA}$, $V_{CEQ} \approx 4.4 \text{ V}$
(2) $A_v \approx -27.2$, $R_i = 15.55 \text{ k}\Omega$, $R_o \approx 10 \text{ k}\Omega$
- 4.5.1 共集电极组态; v_o 波形有错
- 4.5.2 (1) $I_{BQ} \approx 23 \mu\text{A}$, $I_{CQ} = 1.15 \text{ mA}$, $V_{CEQ} = -6.13 \text{ V}$
(2) $A_v \approx 0.99$, $R_i \approx 87.3 \text{ k}\Omega$, $R_o = 36 \Omega$
(3) $v_o \approx 197 \text{ mV}$
- 4.5.3 (1) $I_{BQ} \approx 18 \mu\text{A}$, $I_{CQ} = 1.8 \text{ mA}$, $V_{CEQ} = 2.8 \text{ V}$
(2) $A_{v1} \approx -0.79$, $A_{v2} \approx 0.8$
(3) $R_i \approx 8.2 \text{ k}\Omega$
(4) $R_{o1} \approx 2 \text{ k}\Omega$, $R_{o2} \approx 31 \Omega$
- 4.5.4 $A_v \approx 268$, $R_i \approx 28 \Omega$, $R_o \approx 7.5 \text{ k}\Omega$
- 4.5.5 ① $A_v = -\beta R_e / [r_{be} + (1 + \beta)R_e]$, $R_i = r_{be} + (1 + \beta)R_e$, $R_o \approx R_c$
② $A_v = \beta R_e / [r_{be} + (1 + \beta)R_e]$, $R_i = R_e + r_{be} / (1 + \beta)$, $R_o \approx R_c$
③ $A_v = (1 + \beta)R_e / [r_{be} + (1 + \beta)R_e]$, $R_i = r_{be} + (1 + \beta)R_e$, $R_o = R_e \parallel [r_{be} / (1 + \beta)]$
- 4.5.6 (1) $V_{BQ} = -0.1 \text{ V}$, $V_{EQ} = -0.8 \text{ V}$, $V_{CQ} = 2 \text{ V}$
(2) $r_{be} \approx 2.83 \text{ k}\Omega$
(3) $A_{vs} \approx -28.42$
(4) $A_{vs} \approx 19.47$
(5) $A_{vs} \approx 0.08$
- 4.6.1 (1) $I_{CQ1} \approx I_{CQ2} \approx 10.2 \text{ mA}$, $V_{CEQ1} = 6 \text{ V}$, $V_{CEQ2} = 4.9 \text{ V}$
(2) $A_{v1} \approx -1$, $A_{v2} \approx 102$, $A_v = -102$, $R_i \approx r_{be1} = 0.46 \text{ k}\Omega$, $R_o \approx R_{c2} = 0.47 \text{ k}\Omega$
- 4.6.2 (1) $I_{BQ1} \approx 1.04 \mu\text{A}$, $I_{CQ1} \approx 1.04 \text{ mA}$, $V_{CEQ1} \approx 7.6 \text{ V}$
 $I_{BQ2} \approx 27 \mu\text{A}$, $I_{CQ2} \approx 2.7 \text{ mA}$, $V_{CEQ2} \approx 6 \text{ V}$
(2) $A_v \approx -182$, $R_i \approx 1.88 \text{ k}\Omega$, $R_o \approx 61 \Omega$
- 4.6.3 (1) CC-CB 组态
(2) $I_{CQ1} \approx I_{CQ2} \approx 1.33 \text{ mA}$, $V_{CEQ1} = 6.7 \text{ V}$, $V_{CEQ2} \approx 3.8 \text{ V}$
(3) $R_i \approx 2.4 \text{ k}\Omega$, $A_v = 0.5$, $A_{v1} = 46$, $R_o \approx R_{c2} = 2.2 \text{ k}\Omega$
- 4.7.1 (1) $|\dot{A}_{VM}| = 1000$, $f_L = 100 \text{ Hz}$, $f_H = 100 \text{ MHz}$
(2) $|\dot{A}_v| (\text{dB}) = 57 \text{ dB}$
- 4.7.2 $f_H = 100 \text{ kHz}$, $f_L = 10 \text{ Hz}$, $|\dot{A}_{VM}| (\text{dB}) = 40 \text{ dB}$, 相位差为 0°
- 4.7.3 $|\dot{A}_M| = 10$, $f_L = 10 \text{ Hz}$, $f_H = 1 \text{ MHz}$, $|\dot{A}| = 1$ 时, f 为 1 Hz 或 10 MHz
- 4.7.4 (1) 不会失真, $V_{om} = 1 \text{ V}$, 相位差为 -180°
(2) 此时 $f = f_H$, 不会失真, $V_{om} = 2.83 \text{ V}$, 相位差为 -225°
(3) 此时 $f = 100 \text{ kHz}$, 超出通带, 但输出波形仍不会失真
- 4.7.5 (1) $f_L = 392 \text{ Hz}$; (2) $V_{om} = 818 \text{ mV}$, 相位差为 -135°
- 4.7.6 $g_m \approx 57.69 \text{ mS}$, $C_{b'e} = 92 \text{ pF}$, $r_{b'e} \approx 866.7 \Omega$, $r_{bb'} = 233.3 \Omega$
- 4.7.7 (a) $f_H \approx 3.13 \text{ MHz}$

(b) 中频电压增益变化约 1.42 倍, 上限频率变化约 0.78 倍, 增益 - 带宽积变化约 1.11 倍

4.7.8 (1) $R_i \approx 5.55 \text{ k}\Omega$; (2) $|A_{vM}| \approx 30.64$; (3) $f_H \approx 1.72 \text{ MHz}$

4.7.9 $f_L \approx 143 \text{ Hz}$

4.8.1 (1) $t_r = 0.0044 \mu\text{s}$; (2) $t_r = 0.035 \mu\text{s}$; (3) $t_r = 0.35 \mu\text{s}$

4.8.2 (1) 平顶降落为 4.16%; (2) $f_{min} = 416 \text{ Hz}$

SP4.9.1 (3) $R_i \approx 743 \Omega$, $R_o \approx 3.12 \text{ k}\Omega$

SP4.9.3 $f_L \approx 10 \text{ Hz}$, $f_H \approx 99.7 \text{ kHz}$, $20\lg A_{vM} = 24 \text{ dB}$, 中频段相位差约为 0°

第 5 章

5.1.1 图 a: N 沟道耗尽型, $V_p = -3 \text{ V}$; 图 b: P 沟道耗尽型, $V_p = 2 \text{ V}$; 图 c: P 沟道增强型, $V_T = -4 \text{ V}$

5.1.2 (1) 增强型; (2) P 沟道; (3) $V_T = -4 \text{ V}$

5.1.3 $v_{GS} = -1.08 \text{ V}$, $v_{DS} = -1.58 \text{ V}$

5.1.4 $I_D = 0.499 \text{ mA}$

5.2.1 $V_{GS} = 2 \text{ V}$, $I_D = 0.1 \text{ mA}$, $V_{DS} = 2 \text{ V}$

5.2.2 $I_D = -0.45 \text{ mA}$, $V_{DS} = -1.625 \text{ V}$

5.2.3 $A_v \approx -8.24$, $A_{vs} \approx -8.1$

5.2.4 $A_v \approx -12.78$

5.2.5 $R_i = 120 \text{ k}\Omega$, $A_{vs} = 0.86$, $R_o \approx 80 \Omega$

5.2.6 $A_v = -200$

5.2.7 $A_v = -175$

5.2.8 $A_v = -5$

5.2.9 (2) $\dot{A}_v = -3.3$; (3) $R_i \approx 2075 \text{ k}\Omega$

5.3.3 N 沟道 JFET, $V_p = -4 \text{ V}$, $I_{DSS} = 3 \text{ mA}$

5.3.5 图 a: P 沟道, JFET; 图 b: N 沟道, 耗尽型 MOSFET; 图 c: P 沟道, 耗尽型 MOSFET; 图 d: N 沟道, 增强型 MOSFET

5.3.6 (1) 用图解法得, $V_{GSQ} \approx -0.35 \text{ V}$, $I_{DQ} \approx 0.22 \text{ mA}$, $V_{DSQ} \approx 9.5 \text{ V}$

(2) 用计算得, $V_{GSQ} \approx -0.33 \text{ V}$, $I_{DQ} \approx 0.22 \text{ mA}$, $V_{DSQ} \approx 9.2 \text{ V}$

5.3.7 (1) $I_{DQ} = 1 \text{ mA}$, $R_1 = 2 \text{ k}\Omega$; (2) $R_{2max} = 6 \text{ k}\Omega$; (3) $\dot{A}_v \approx -1.1$ (忽略 R_g 影响), $R_o \approx R_d = 10 \text{ k}\Omega$

5.3.8 $A_v \approx 0.92$, $R_i \approx 2075 \text{ k}\Omega$; $R_o \approx 1.02 \text{ k}\Omega$

5.5.1 $A_v \approx 0.89$, $R_i \approx 5.1 \text{ M}\Omega$

5.5.4 T₁——共漏, T₂——共射, $A_{v1} \approx \frac{g_m r_{be}}{1 + g_m r_{be}}$, $A_{v2} \approx \frac{-\beta(R_C \parallel R_L)}{r_{be}}$

$A_v \approx A_{v1} A_{v2}$, $R_i \approx R_g$, $R_o = R_C$

SP5.6.1 (1) 约为 0.2 mA; (2) 约为 1.375 3 V; (3) -169.5 倍

SP5.6.2 (1) $I_D = 1.02 \text{ mA}$, $V_{GS} = -1.09 \text{ V}$, $V_{DS} = 7.73 \text{ V}$

(3) $BW \approx 10.45$ MHz, $R_i \approx 2$ M Ω , $R_o \approx 1.958$ k Ω

SP5.6.3 (1) $I_D = 0.299$ mA, $V_{GS} = -2.52$ V, $V_{DS} = 7.72$ V

第6章

6.1.1 $I_0 = 19.4$ mA

6.1.2 $r_o = r_{ce2}(1 + \beta_2)$

6.1.3 $R = 2.21$ k Ω , $I_3 = 1$ mA, $I_4 = 0.5$ mA

6.1.4 $A_v = -200$

6.1.5 $I_{REF} = 1.35$ mA, $I = 4.05$ mA

6.2.1 (1) $I_{C1} = I_{C2} = 0.5$ mA, $V_{CE1} = V_{CE2} = 5.7$ V

(2) $A_{vd} = -188.7$, $A_{vd1} = -94.35$, $A_{vc1} = -0.2$, $K_{CMR1} = 471.75$

6.2.2 (1) $v_o = -0.87$ V; (2) $v'_o = -0.29$ V; (3) $v_{o2} = 0.43$, $A_{vd2} = 21.7$, $A_{vc2} = -0.028$, $K_{CMR2} \approx 775$; (4) $R_{id} = 25.8$ k Ω , $R_{ie} = 10.1$ M Ω , $R_{oe} = 5.6$ k Ω

6.2.3 $R_{id} = 660.7$ k Ω , $A_{vd1} = -28$, $A_{vc1} = -0.63$, $K_{CMR1} = 44.4$

6.2.4 $A_{vd2} = 12$, $A_{vc2} = -0.0005$, $K_{CMR2} = 24000$, $R_{id} = 13.5$ k Ω , $R_o = 4.7$ k Ω

6.2.5 (1) $I_C = 0.52$ mA, $I_B = 10$ μ A, $V_{CE} = 4$ V

(2) $v_{id} = 0.061$ V, $v_{s1} = 0.0305$ V, $v_{s2} = -0.0305$ V

6.2.6 (1) $I_{REF} = 2.4$ mA, $I_0 = 1.2$ mA, $I_{C1} = I_{C2} = 0.6$ mA

(2) $A_{vd2} = 1823$, $A_{vc2} = 0.163$, $K_{CMR2} = 11.18 \times 10^3$

(3) $R_{id} = 9.8$ k Ω , $R_{oe} = 83.5$ k Ω

6.2.7 $A_{vd2} = 112$

6.2.8 (1) $I_{REF} = I_0 = 10$ μ A, $I_{D1} = I_{D2} = 5$ μ A

(2) $v_{o2} = 600$ μ V, $A_{vd2} = 60$, $A_{vc2} = -0.1$, $K_{CMR2} = 600$

6.2.10 (1) $A_{vd2} = 14.1$, $A_{vc2} = -4.7 \times 10^{-3}$, $K_{CMR2} = 3000$; (2) $v_{o2} = 563.86$ mV

6.2.11 $A_{vd2} = 35.258$, $v_{o2} = 1410$ mV, $A_{vc2} = -6.25 \times 10^{-3}$, $K_{CMR2} = 5.64 \times 10^3$

6.3.2 v_{o1} 和 v_{o2} 的幅值范围为 9.1 V, $v_o = v_{o1} - v_{o2}$ 的幅值为 9.1 V

6.5.1 $R_2 = 93.75$ k Ω

6.5.2 (1) $V_o = -100$ mV; (2) $R_2 = 90.9$ k Ω ; (3) $V_o = -20$ mV; (4) $V_o = \pm 55$ mV;

(5) $V_o = (-20 \pm 55)$ mV

6.5.3 $I_C = 20.7$ nA

6.5.4 $f_H = 100$ kHz, $BW_p = 15.9$ kHz

6.5.5 (1) $V_{or} = 5.506$ V; (2) $V_{or} = 505$ mV; (3) $T = 94.3$ °C

$$6.6.2 v_o = \sqrt[3]{\frac{-v_i}{K^2}}$$

6.6.3 (1) $v_{o1} = Kv_{s1}^2$, $v_{o2} = Kv_{s2}^2$, $v_o = -K(v_{s1}^2 + v_{s2}^2)$; (2) $v_o = -Kv_{sm}^2$

$$6.6.4 A_{vf}(s) = -\frac{R_2}{R_1} \cdot \frac{1}{1 + \frac{sR_2C}{KV_c}}, f_c = \frac{KV_c}{2\pi R_2 C}, f_0 = 39.8 \text{ Hz} \sim 79.6 \text{ Hz}$$

SP6.8.1 (2) -123.2, -0.0323, 3814.24

SP6.8.2 (1) $I_{\text{REF}} = 12.08 \mu\text{A}$, $I_0 = 11.41 \mu\text{A}$, $I_{D1} = I_{D2} = 5.71 \mu\text{A}$, $V_{D1} = V_{D2} = 2.338 \text{ V}$
(2) 51.87, -0.009136

第7章

7.2.3 (2) $i_o \approx -v_i/R_3$; (3) 压控电流源

7.3.1 $v_i = 0.1 \text{ V}$, $v_f = 0.099 \text{ V}$, $v_{id} = 0.001 \text{ V}$

7.3.2 $A_1 A_2 / (1 + A_1 A_2 F_1 + A_2 F_2)$

7.3.3 $F_v = 0.098$, $A_{vf} \approx 10.2$

7.4.1 0.05%

7.5.1 $A_{vf} \approx 1 + R_f/R_{b2}$

7.5.2 (a) $A_{rf} \approx -R_2$, $A_{vf} \approx -R_2/R_1$

(b) $A_{gf} \approx 1/R_{e1}$, $A_{vf} \approx -(R_{e3} \parallel R_{e2})/R_{e1}$

(c) $A_{if} \approx 1 + R_f/R_{e2}$, $A_{gf} \approx R_{e2}(R_f + R_{e2})/R_s R_{e2}$

(d) $A_{vf} \approx 1 + R_2/R_1$

7.5.3 $A_{rf} \approx -[R_{e4}(R_{e2} + R'_{e4}) + R_{e2}R'_{e4}]/R'_{e4}$

7.7.1 8 kHz

7.7.2 带宽为 50 kHz, 增益 - 带宽积为 5 MHz

7.8.1 (2) $20\lg |A_{vM}F_v|_{\max} = 18 \text{ dB}$; (3) 不能稳定工作

7.8.2 F_v 的变化范围是 $10^{-4} \sim 10^{-5}$; 环路增益的最大值是 20 dB

* 7.8.3 $F_v = 0.02 \sim 0.00001$, 环路增益约为 1995.3

SP7.9.1 $A_{vf} = 6$, $R_{if} = 1.664 \times 10^{10} \Omega$, $R_{of} = 0.00605 \Omega$

SP7.9.2 $A_{gf} = 82.53 \text{ mS}$, $R_{if} = 1.62 \text{ M}\Omega$, $R_{of} = 1.486 \text{ M}\Omega$

SP7.9.3 (1) 约为 980 kHz; (2) 约为 1 MHz

第8章

8.3.1 (1) $P_{om} \approx 2.07 \text{ W}$; (2) $R_b \approx 1570 \Omega$; (3) $\eta \approx 24\%$

8.3.2 (1) $P_{om} = 4.5 \text{ W}$; (2) $P_{CM} \geq 0.9 \text{ W}$; (3) $|V_{(BR)CEO}| \geq 24 \text{ V}$

8.3.3 (1) $V_{CC} \geq 12 \text{ V}$; (2) $I_{CM} \geq 1.5 \text{ A}$; $|V_{(BR)CEO}| \geq 24 \text{ V}$; (3) $P_V \approx 11.46 \text{ W}$;
(4) $P_{CM} \geq 1.8 \text{ W}$; (5) $V_i \approx 8.49 \text{ V}$

8.3.4 (1) $P_o = 12.25 \text{ W}$; $P_{T1} = P_{T2} = 5.02 \text{ W}$, $P_V = 22.29 \text{ W}$, $\eta \approx 54.96\%$

(2) $P_o = 25 \text{ W}$; $P_T = 2P_{T1} \approx 6.85 \text{ W}$, $P_V = 31.85 \text{ W}$, $\eta \approx 78.5\%$

8.4.1 $V_{CC} \geq 24 \text{ V}$

8.4.2 $P_{om} = 2.25 \text{ W}$

8.4.3 (1) $V_{C2} = 6 \text{ V}$, 调整 R_1 或 R_3

(2) 增大 R_2

(3) $P_{T1} = P_{T2} = 1.156 \text{ mW} \gg P_{CM}$, 会烧坏功放管

8.4.4 (1) $P_o = 3.54 \text{ W}$; (2) $P_V \approx 5 \text{ W}$

- 8.4.5 $P_o = 16 \text{ W}$; $P_v \approx 21.6 \text{ W}$, $P_T \approx 5.6 \text{ W}$, $\eta \approx 74.1\%$
- 8.4.8 管子集电极输出功率 $P_{oc} = 53.4 \text{ mW}$, 负载上得到的功率 $P_o = 42.7 \text{ mW}$, 总效率 $\eta \approx 40\%$
- 8.4.9 (1) 管子集电极输出功率 $P_{oc} = 9 \text{ W}$, 负载上得到的功率 $P_o = 7.2 \text{ W}$, $P_v \approx 11.5 \text{ W}$, $\eta \approx 62.6\%$
(2) 通过管子的最大电流 $I_{Cmax} = 1.5 \text{ A}$, 管子承受的最大反向电压 $|V_{CEmax}| = 24 \text{ V}$, 每只管子的最大管耗 $P_{T1} = P_{T2} = 1.25 \text{ W}$, 未超过定额, 可用
- 8.5.1 (1) $P_{om} \approx 5.1 \text{ W}$; (2) $V_i \approx 64 \text{ mV}$
- 8.5.2 (1) $P_{om} = 14.06 \text{ W}$; (2) $P_v \approx 17.9 \text{ W}$, $\eta \approx 78.5\%$
- 8.5.3 (1) $A_{v1} = 2.5$, $A_{v2} = -2.5$; (2) $P_{om} \approx 0.28 \text{ W}$; (3) $V_{im} \approx 5.2 \text{ V}$
- SP8.6.1 $P_{om} = 3.6952 \text{ W}$, $P_{TIm} = 1.1036 \text{ W}$
- SP8.6.2 32 V
- SP8.6.3 (1) $P_o = 2.72 \text{ W}$; (2) 电源供给的功率 $P_v = 4.8 \text{ W}$

第9章

- 9.1.1 (1) 带通; (2) 低通; (3) 带阻; (4) 高通
- 9.1.2 (1) 带阻; (2) 低通; (3) 高通; (4) 带通
- 9.2.2 (2) $|A_V(j\omega)| = 1$, $\varphi = -\pi - 2\arctan(\omega RC)$
- 9.3.1 $\omega_H = \omega_C = 100 \text{ rad/s}$, $A_{VF} = A_0 = 1.586$
- 9.3.2 $\omega_0 = 10^4 \text{ rad/s}$, $f_0 = 1592 \text{ Hz}$, $BW = \omega_0/2\pi Q \approx 2347 \text{ Hz}$
- 9.3.3 (1) $A_1(s) = -\frac{sCR_1}{1+sCR_1}$, $A(s) = -\frac{1}{1+sCR_1}$
(2) A_1 ——阶高通, 整个电路组成一阶低通
- 9.3.4 $\frac{V_o(s)}{V_i(s)} = -\frac{sCR_1}{1+sCR_1}$, 一阶高通
- 9.3.5 $\frac{V_o(s)}{V_i(s)} = \frac{-sC_1R_f}{1+s(C_1R_1 + C_fR_f) + s^2C_1C_fR_1R_f}$, 带通
- 9.3.6 (1) 高通; (2) $A_0 = -1$, $\omega_c = \frac{1}{C\sqrt{R_1R_2}}$, $Q = \frac{1}{3}\sqrt{\frac{R_1}{R_2}}$
- 9.3.7 $A_{VF} = 3 - \frac{1}{Q} = 2$, 峰值 $|A(j\omega)|_{max} = 2.828$, 对应的角频率 $\omega = 2\sqrt{2}\pi \times 200 \text{ rad/s}$
- 9.3.9 (1) 二阶低通; (2) 三阶低通; (3) 三阶高通
- 9.6.2 (2) $R_f \geq 2R_{el}$, $f_0 \approx 58.5 \text{ Hz}$
- 9.6.4 R_2 断开时, v_o 近似为方波, 峰-峰值为 20 V
- 9.6.5 $R_p \approx 3.55 \text{ k}\Omega$
- 9.6.6 (2) $R_p + R_2 > 2R_1 = 10.2 \text{ k}\Omega$; (3) $f_0 \approx 1591.5 \text{ Hz}$
- 9.6.8 (2) $V_{om} \approx 8.35 \text{ V}$; (3) $R_2 = 0$, 电路停振; (4) R_2 开路, v_o 近似为方波, 峰-峰值约为 28 V

9.7.3 (1) 图 9.7.3a 的 $f_0 \approx \frac{1}{2\pi \sqrt{LC_3}}$

(2) 图 9.7.3b 的 $f_0 \approx \frac{1}{2\pi \sqrt{L(C_3 + C_4)}}$

9.8.1 (1) $v_0 = 0$; (2) $v_0 = 6$ V

9.8.4 $V_T = 1$ V

9.8.5 $V_{T+} = 3$ V, $V_{T-} = -3$ V, $V_{OH} = 9$ V, $V_{OL} = -9$ V

9.8.9 $f = \frac{R_2}{4R_1 RC} = 3067.6$ Hz

9.8.10 (1) $v_{o1} = -0.15$ V; (2) $v_{o2} = 1.5$ V, $v_{o3} = 6$ V

SP9.9.3 (1) 和 (2) 分别为二阶和三阶低通滤波器; (3) 为高通滤波器; (4) 为全通滤波器; (5) 为带通滤波器

SP9.9.4 振荡频率约为 1.053 kHz

SP9.9.5 振荡频率约为 353 kHz

SP9.9.6 (2) 上、下限门限电压约为 3.2 V

SP9.9.7 振荡频率约为 3 kHz

第 10 章

10.1.1 (2) $V_L = 0.9V_2$, $I_L = 6.9 V_2/R_L$; (3) $I_D = I_L/2$, $V_{RM} = 2\sqrt{2}V_2$; (4) $V_{2a} = V_{2b} = 33.3$ V, $I_D = 40$ mA, $V_{RM} = 94.2$ V, 选用 2CP6A ($I_{DM} = 100$ mA, $V_{RM} = 100$ V)

10.1.2 (1) $V_{L1} = 45$ V, $I_{L1} = 4.5$ mA, $V_{L2} = 9$ V, $I_{L2} = 90$ mA; (2) $I_{D1} = I_{L1} = 4.5$ mA, $V_{RM} = 141$ V, $I_{D2} = I_{D3} = 45$ mA, $V_{RM2} = V_{RM3} = 28.2$ V

10.1.3 (1) $I_D = 240$ mA, $V_{RM} = 28.2$ V, 选用 2CP1D ($I_{DM} = 500$ mA, $V_{RM} = 100$ V)

(2) $C = 1000 \mu\text{F}$, 耐压 $V_{CM} > 28.2$ V, 选用 1000 $\mu\text{F}/50$ V 电解电容

(3) $V_2 = 20$ V, $I_2 = 720$ mA

10.1.4 $V_{RM} = V_{CRM} = 2\sqrt{2}V_2$, $V_{L1} = 4\sqrt{2}V_2$, $V_{L2} = 3\sqrt{2}V_2$

10.1.5 (1) v_i 瞬时极性为正时, D_3 、 D_1 导通, 电流从 A 流向 B

(2) $I_M = (0.9V_i)/R$

(3) $R = 9$ kΩ

(4) $R = 10$ kΩ

10.2.1 (1) D_z 接反, D_z 正向导通, $V_o = 0.7$ V; $R = 0$ 时, D_z 损坏

(2) $V_2 = 15$ V, $V_o = 6$ V

(3) $R_o = r_z = 20$ Ω, $\Delta V_o / \Delta V_i = 0.02$

10.2.2 (2) $V_{REF} = 7$ V, 电压极性为正

10.2.3 (3) $V_{Omin} = 15$ V, $V_{Omax} = 20$ V; (4) $V_{CE1max} = 18$ V; (5) $P_{Cl} = 5.4$ W

10.2.6 (1) $R_1 = (240 \sim 120)$ Ω

(2) $V_o = 18.3$ V; $R_2 = 6.3$ kΩ; $V_{Imin} = 39$ V

(4) $V_o = (1.2 \sim 36.6)$ V